

**In the Specification**

At page 1, lines 2 – 4, please replace the paragraph as follows (underlined denotes replacements additions and double bracket notes deletions):

[["]]This is a Divisional of Application Serial No. 09/107,111, now U.S. Patent 5,972,727 filed June 30, 1998, which application(s) are incorporated herein by reference.[["]]

At page 1, lines 15 – 25 and page 2, lines 1 - 3 please replace the paragraph as follows (underlined denotes replacements additions and strikethrough notes deletions):

Manufacturers pay particular attention to the photolithography process, a process which occupies a substantial amount of floor space and is performed on a given wafer a number of different times throughout the fabrication process. The photolithography process typically involves applying a photoresist layer (e.g., SiO<sub>2</sub>) over the surface of a semiconductor wafer using a coating machine or coater. The wafer then moves to an exposure tool, such as a photolithography stepper, which exposes the photoresist layer to a patterned light source. The light source is typically patterned using a mask or reticle (hereinafter reticle). The reticle typically contains clear and opaque features which generally define the pattern to be created in the photoresist layer. The exposed photoresist is then developed and regions of the photoresist are dissolved such that the pattern is transferred to the photoresist layer. The exposed regions of the underlying semiconductor wafer layer are then processed by, for example, etching the exposed wafer layer, depositing a material on the exposed wafer layer, or doping the exposed wafer layer.